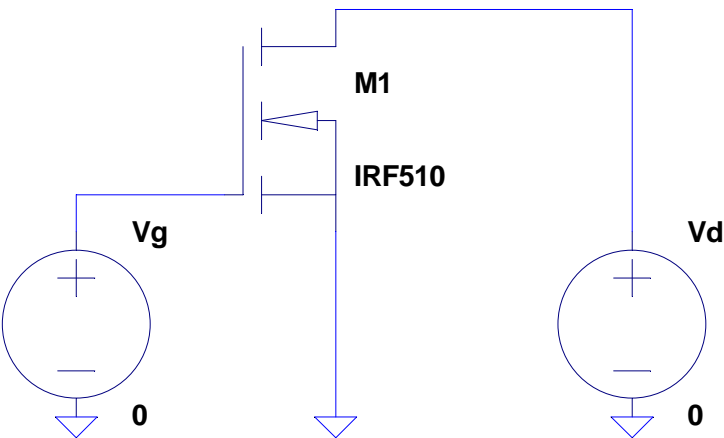


TRANSCEIVER CW F8EOZ - IRF510 CURVE - V 23/11/2013 11:35
N-Channel enhancement mode silicon gate power field effect transistor

Output characteristic curves: Drain current vs Drain-to-Source voltage
ID = f(VDS) | VGS = parameter



```
.dc Vd 0 14 1 Vg 4.5 8 0.5
```

From Fairchild datasheet...
Drain to Source Voltage VDS 100 V
Drain to Gate Voltage (RGS= 20k) VDGR 100 V
Continuous Drain Current ID 5.6 A TC= 100°C ID 4A
Pulsed Drain Current IDM 20 A
Gate to Source Voltage VGS ±20 V
Maximum Power Dissipation PD 43 W
Linear Derating Factor 0.29 W/°